Abstract

SEMICONDUCTOR DIE AND METHOD OF FORMING NOISE ABSORBING REGIONS BETWEEN THVS IN PERIPHERAL REGION OF THE DIE

A semiconductor wafer has a plurality of semiconductor die. A peripheral region is formed around the die. An insulating material is formed in the peripheral region. A portion of the insulating material is removed to form a through hole via (THV). A conductive material is deposited in the THV to form a conductive THV. A conductive layer is formed between the conductive THV and contact pads of the semiconductor die. A noise absorbing material is deposited in the peripheral region between the conductive THV to isolate the semiconductor die from intra-device interference. The noise absorbing material extends through the peripheral region from a first side of the semiconductor die to a second side of the semiconductor die. The noise absorbing material has an angular, semi-circular, or rectangular shape. The noise absorbing material can be dispersed in the peripheral region between the conductive THV.

(Figure 4)